

REMARKS/ARGUMENT

Claims 1 and 2 have been cancelled without prejudice.

Claims 4-10 are new. Entry and consideration of claims 4-10 are requested.

EXPRESS MAIL CERTIFICATE

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January 28, 2003

Date of Signature

Respectfully submitted,

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APPENDIX A
"CLEAN" VERSION OF EACH PARAGRAPH/SECTION/CLAIM
37 C.F.R. § 1.121(b)(ii) AND (c)(i)

SPECIFICATION:

Replacement for paragraph [0006] at page 2, line 1:

B1 A process and structure which prevents punch-through without increasing channel dose
or channel depth would be very desirable.

CLAIMS:

4. (NEW) A method for producing a vertical MOSFET, the method comprising:
selecting an active region in a major surface of a semiconductor body of a first
conductivity type;

B2 cont implanting dopants of a second conductivity type in all of said active region;
forming a plurality of spaced channel region of said second conductivity type in said
active region; and

forming at least one source region of said second conductivity type in each of said
channel regions.

5. (NEW) The method of claim 4 further comprising, forming gate structures
adjacent each channel region, each gate structure comprising a gate oxide formed over said active
region and a respective gate electrode disposed over said gate oxide.

6. (NEW) The method of claim 4 further comprising, forming a field oxide layer
over said major surface of said semiconductor body and opening a window to expose said active
region.

7. (NEW) The method of claim 6, wherein said dopants of said second conductivity
type are implanted through said window in said field oxide layer.

8. (NEW) The method of claim 4, wherein said dopants of said second conductivity type are comprised of boron.

9. (NEW) The method of claim 4, wherein said dopants of said second conductivity type are comprised of one of arsenic and phosphorous.

10. (NEW) The method of claim 5 further comprising, forming depositing and oxide interlayer over said active region; opening windows over at least said source regions; and forming a source contact over said active region.

B2
End

APPENDIX B
VERSION WITH MARKINGS TO SHOW CHANGES MADE
37 C.F.R. § 1.121(b)(iii) AND (c)(ii)

SPECIFICATION:

Paragraph [0006] at page 2, line 1:

Sub C1 A process and structure which prevents [punch-through] punch-through without increasing channel dose or channel depth would be very desirable.